

# N-channel 60 V 3.0 mΩ standard level MOSFET Rev. 02 — 28 October 2010 P

Product data sheet

#### **Product profile** 1.

### **1.1 General description**

Standard level N-channel MOSFET in a TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

#### Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Static char	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12		-	2.4	3	mΩ
Dynamic c	haracteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 80 \text{ A}; \text{ V}_{DS} = 12 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>		-	28	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy			-	-	800	mJ

[1] Continuous current is limited by package.

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### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

### 3. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R0-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

### 4. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

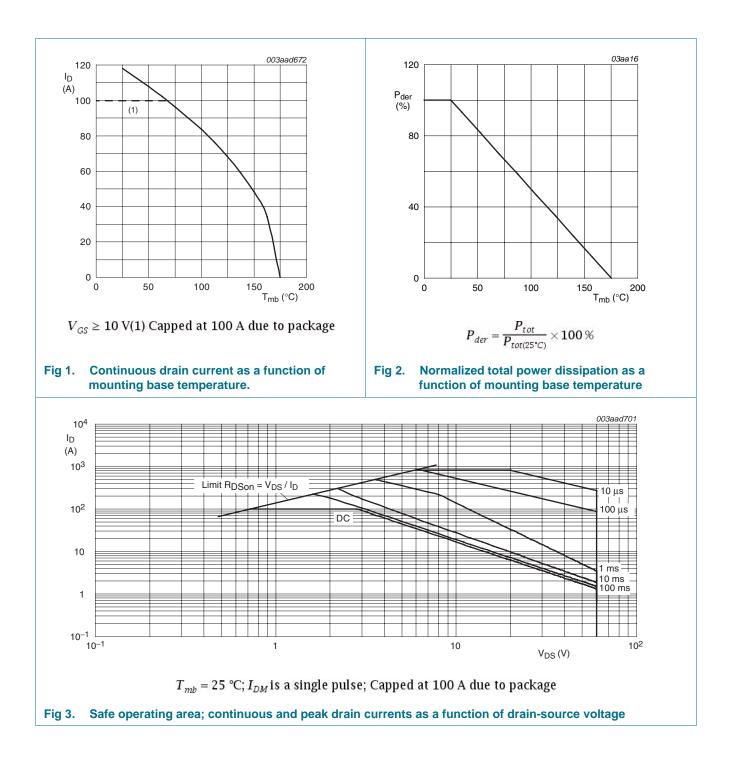
Symbol	Parameter	Conditions	ſ	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-		60	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-		60	V
V <sub>GS</sub>	gate-source voltage		-	·20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	•	83.4	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	•	100	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	•	824	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	•	306	W
T <sub>stg</sub>	storage temperature		-	-55	175	°C
Tj	junction temperature		-	-55	175	°C
Source-drai	in diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u> -		100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-		824	А
Avalanche ı	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; unclamped	-	•	800	mJ

[1] Continuous current is limited by package.

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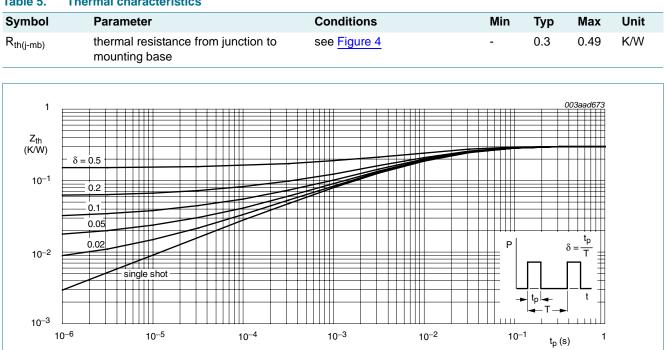
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### 5. Thermal characteristics



#### Table 5.Thermal characteristics

Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

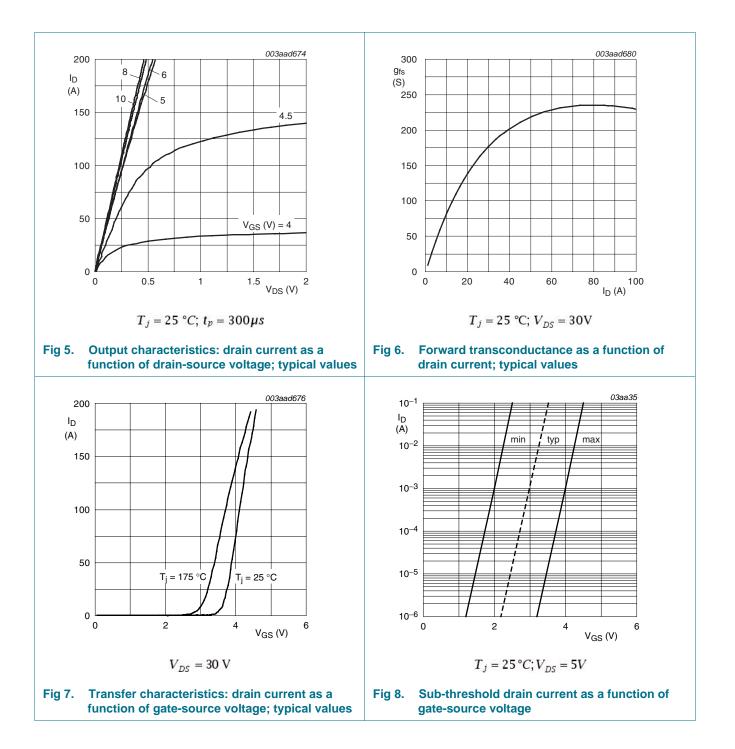
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### 6. Characteristics

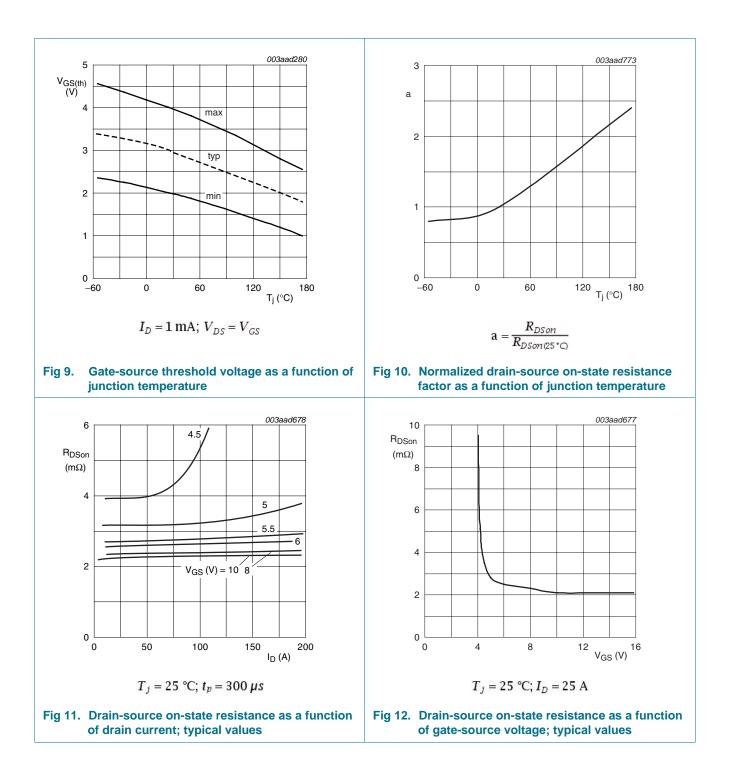
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = -55 °C	54	-	-	V
	voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	2	3	4	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 9	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 9</u>	-	-	4.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 10</u>	-	-	7.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	2.4	3	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 80 A; $V_{DS}$ = 12 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	130	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 80 A; $V_{DS}$ = 12 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 13</u>	-	43	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 80 A; $V_{DS}$ = 12 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	28	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{\text{See } \frac{\text{Figure } 16}{100000000000000000000000000000000000$	-	8079	-	pF
C <sub>oss</sub>	output capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	971	-	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 15</u> ; see <u>Figure 16</u>	-	492	-	pF
d(on)	turn-on delay time	$V_{DS}$ = 30 V; $R_L$ = 0.5 Ω; $V_{GS}$ = 10 V;	-	31	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$	-	26	-	ns
d(off)	turn-off delay time		-	77	-	ns
t <sub>f</sub>	fall time		-	22	-	ns
Source-drai	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.88	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs;	-	54	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 V; V_{DS} = 30 V$	_	97		nC

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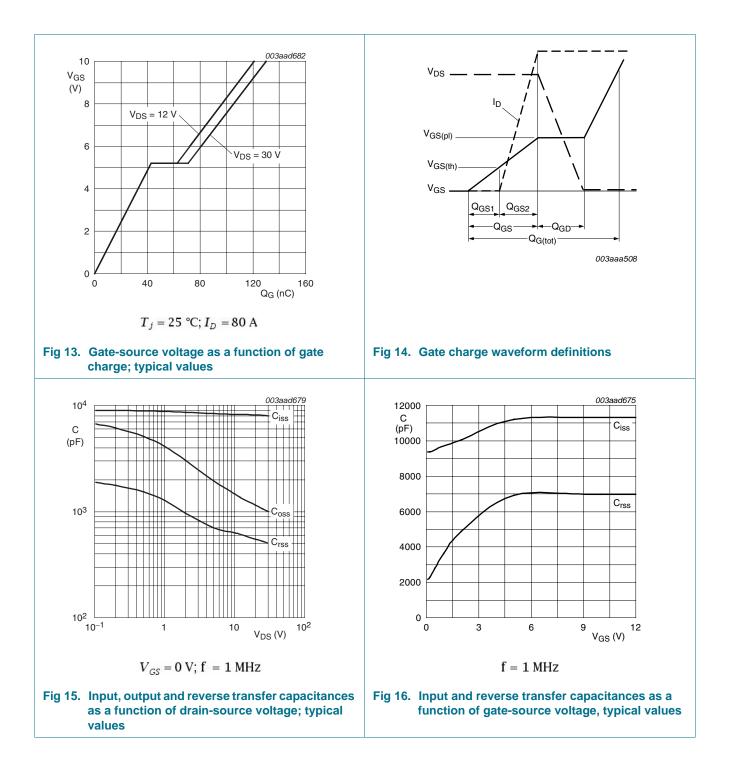
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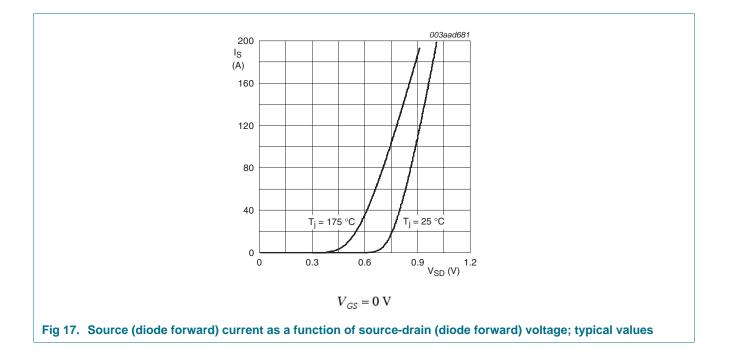
# **PSMN3R0-60PS**



# PSMN3R0-60PS



# **PSMN3R0-60PS**



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#### **Package outline** 7.

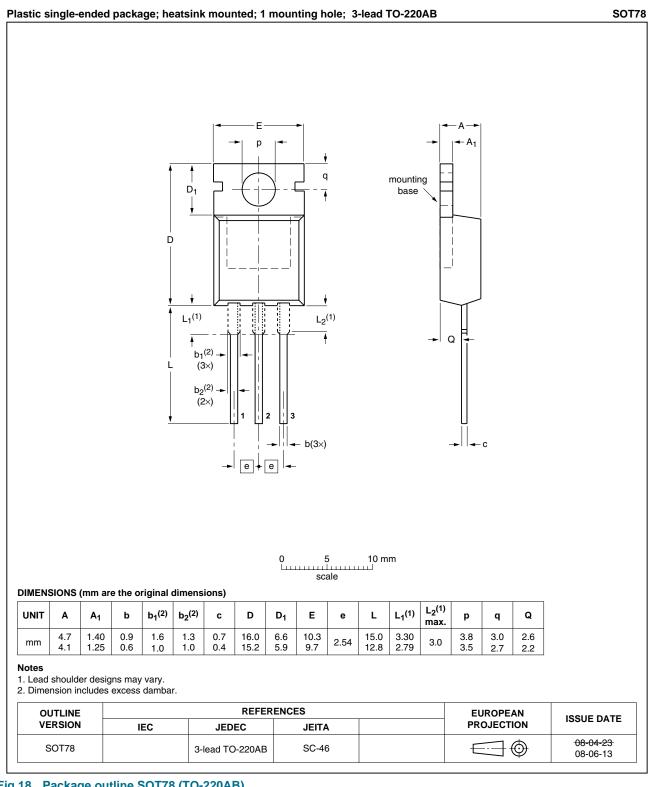


Fig 18. Package outline SOT78 (TO-220AB)

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## 8. Revision history

Table 7. Revision h	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R0-60PS v.2	20101028	Product data sheet	-	PSMN3R0-60PS v.1
Modifications:	<ul> <li>Various changes</li> </ul>	s to content.		
PSMN3R0-60PS v.1	20091123	Product data sheet	-	-

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### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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